2SD882

TO-92 Plastic-Encapsulate Transistors

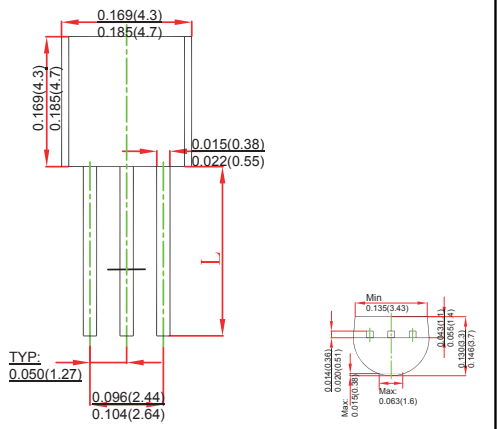
Features

- Switching and amplification in high voltage Applications such as telephony
- NPN Transistors

MECHANICAL DATA

- Case style:TO-92 molded plastic
- Mounting position:any

TO-92



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current –Continuous	3	A
P_C	Collector Power Dissipation	1.25	W
T_J	Junction Temperature	-65-150	°C
T_{stg}	Storage Temperature	-65-150	°C

PACKAGE INFORMATION

Device	Package	Shipping
2SD882	TO-92	2000/Tape&Reel

Characteristic	Symbol	Test conditions	Min	Typ	Max	Unit
Collector −Emitter Breakdown Voltage	V(BR)ceo	Ic=-1mA	30			V
Collector −Base Breakdown Voltage	V(BR)cbo	Ic=-1mA	40			V
Emitter −Base Breakdown Voltage	V(BR)ebo	Ic=-1mA	6			V
Collector Cutoff Current	Icbo	Vcb=-40V			0.5	uA
Collector−Emitter Cutoff Current	Iceo	Vce=-30V			1.0	uA
Emitter Cutoff Current	Iebo	Veb=-6V			0.1	uA
DC current gain	HFE	Vce=-5V,Ic=-1mA	200		400	
Collector −Emitter Saturation Voltage	VCE(sat)	Ic=-2A,Ib=-200mA			0.5	V
Base −Emitter Saturation Voltage	VBE(sat)	Ic=-2A,Ib=-200mA			2.0	V
Cutoff Frequency	fT	Vce=10V,Ic=50mA,f=30MHZ	50			MHZ
Input Capacitance	Cibo	-				
Output Capacitance	Cobo	-				
Turn−on Time	ton	-				
Turn−off Time	toff	-				
Storage time	ts	-				